### REPORT DOCUMENTATION PAGE

Form Approved OMB NO. 0704-0188

The public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggesstions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington VA, 22202-4302. Respondents should be aware that notwithstanding any other provision of law, no person shall be subject to any oenalty for failing to comply with a collection of information if it does not display a currently valid OMB control number.

PLEASE DO NOT RETURN YOUR FORM TO THE ABOVE ADDRESS.

			1				
	ATE (DD-MM-YY	YYY)	2. REPORT TYPE		3. DATES COVERED (From - To)		
25-09-2008			Final Report		1-Aug-2006 - 31-Jul-2008		
4. TITLE AN	D SUBTITLE			5a. CO	NTRACT NUMBER		
Permalloy Film Array Spin Dynamics and High Performance Integrated Microwave Devices		W911N	NF-06-1-0335				
			5b. GR	ANT NUMBER			
				5c. PROGRAM ELEMENT NUMBER			
				61110	2		
6. AUTHORS				5d. PROJECT NUMBER			
Pingshan Wa	ing			5e. TA	5e. TASK NUMBER		
				5f. WORK UNIT NUMBER			
7. PERFORM	IING ORGANIZA	TION NAMES A	ND ADDRESSES	•	8. PERFORMING ORGANIZATION REPORT		
Clemson Uni	-				NUMBER		
-	onsored Programs						
300 Brackett Clemson, SC		2963	4 -5702				
Clemson, SC 29634 -5702  9. SPONSORING/MONITORING AGENCY NAME(S) AND				10. SPONSOR/MONITOR'S ACRONYM(S)			
ADDRESS(E	S)				ARO		
U.S. Army Re					11. SPONSOR/MONITOR'S REPORT		
P.O. Box 12211 Research Triangle Park, NC 27709-2211			NUMBER(S) 51903-MS.1				
Kesearch The	angle I alk, NC 27				5 1903-M5. I		
	JTION AVAILIBI						
Approved for	Public Release; Dis	stribution Unlimite	ed				
	MENTARY NOTE						
		•	as report are those of the authors designated by other documents		not contrued as an official Department		
1.4 A DOTED A							
14. ABSTRAC		ect include (1) th	e highest permallov (Pv) ar	ray FMR frequ	ency reported so far without DC		
_			nethod for ferromagnetic ma		* .		
					. Py films are sputtered and		
					Au and Py deposition. Each Py bar		
					arrays are 240 nm and 550 nm, n in these Py structures. The		
15. SUBJEC	ΓTERMS						
microwave de	vices, permalloy th	nin films, spin dyn	amics				
16. SECURIT	Y CLASSIFICATI b. ABSTRACT	ON OF:	17. LIMITATION OF ABSTRACT	15. NUMBE OF PAGES	ER 19a. NAME OF RESPONSIBLE PERSON Pingshan Wang		
U. KEFOKT	U. ABSTRACT	U	SAR		19b. TELEPHONE NUMBER 864-656-2117		
		L			l		

#### Report Title

Permalloy Film Array Spin Dynamics and High Performance Integrated Microwave Devices

#### **ABSTRACT**

Major contributions of this project include (1) the highest permalloy (Py) array FMR frequency reported so far without DC magnetic bias field, and (2) an ultra-sensitive method for ferromagnetic material characterization.

Shape-induced high frequency properties of patterned submicron Py arrays are obtained. Py films are sputtered and patterned on gold (Au) transmission lines. Chromium (Cr) is used as adhesion layers for Au and Py deposition. Each Py bar in the arrays is 10 ?m long and 100 nm thick. The widths of the Py bars in two different arrays are 240 nm and 550 nm, respectively. Micromagnetic simulations indicate single domain magnetization distribution in these Py structures. The measured ferromagnetic resonance frequencies (FMR) without bias field are  $\sim 11.5$  GHz and  $\sim 8$  GHz, respectively.

A new high-frequency method is proposed and demonstrated to significantly reduce parasitic effects through an on-chip interference process. As a result, measurement sensitivity is dramatically improved in comparison with conventional on-chip transmission line FMR methods. On-chip 10-GHz structures were fabricated to experimentally demonstrate a 35-dB sensitivity improvement. To demonstrate the proposed algorithms, a total of 180 patterned micro-Py stripes are used. Reasonable FMR line width and complex permeability are obtained.

# List of papers submitted or published that acknowledge ARO support during this reporting period. List the papers, including journal references, in the following categories:

#### (a) Papers published in peer-reviewed journals (N/A for none)

Pingshan Wang, Hanqiao Zhang, Ralu Divan, Axel Hoffmann, "Tailoring High-Frequency Properties of Permalloy Films via Submicron Patterning", Accepted for publication in IEEE Transactions on Magnetics.

Number of Papers published in peer-reviewed journals:

1.00

#### (b) Papers published in non-peer-reviewed journals or in conference proceedings (N/A for none)

Number of Papers published in non peer-reviewed journals:

0.00

#### (c) Presentations

**Number of Presentations:** 

0.00

#### Non Peer-Reviewed Conference Proceeding publications (other than abstracts):

Number of Non Peer-Reviewed Conference Proceeding publications (other than abstracts):

0

#### Peer-Reviewed Conference Proceeding publications (other than abstracts):

Song, Chunrong; Liu, Zuqin; Eres, Gyula; Geohegan, David B.; Wang, Pingshan; "A New Method for Microwave Characterization of Metallic Single-Walled Carbon Nanotubes,"

Nanotechnology, 2008. NANO '08. 8th IEEE Conference on

18-21 Aug. 2008 Page(s):228 - 229

Zhang, Hanqiao; Song, Chunrong; Divan, Ralu; Hoffmann, Axel; Wang, Pingshan; "High-Frequency Properties of Permalloy Nanowire Arrays for RF Devices,"

Nanotechnology, 2008. NANO '08. 8th IEEE Conference on

18-21 Aug. 2008 Page(s):621 - 624.

Number of Peer-Reviewed Conference Proceeding publications (other than abstracts):

2

#### (d) Manuscripts

Hanqiao Zhang, Chunrong Song and Pingshan Wang, "A new method for high-frequency characterization of patterned ferromagnetic thin films," submitted to Journal of Applied Physics.

#### **Number of Inventions:**

Grad	luata	Cturd	lante
CTENO	шите	20110	ems

<u>NAME</u> Hanqiao Zhang	PERCENT SUPPORTED 1.00	
FTE Equivalent:	1.00	
Total Number:	1	

#### **Names of Post Doctorates**

<u>NAME</u>	PERCENT_SUPPORTED	
FTE Equivalent:		
Total Number:		

#### Names of Faculty Supported

<u>NAME</u>	PERCENT SUPPORTED	
FTE Equivalent:		
Total Number:		

#### Names of Under Graduate students supported

<u>NAME</u>	PERCENT_SUPPORTED	
FTE Equivalent:		
Total Number:		

#### **Student Metrics**

This section only applies to graduating undergraduates supported by this agreement in this reporting period

The number of undergraduates funded by this agreement who graduated during this period: ...... 0.00

The number of undergraduates funded by this agreement who graduated during this period with a degree in science, mathematics, engineering, or technology fields: ..... 0.00

The number of undergraduates funded by your agreement who graduated during this period and will continue

to pursue a graduate or Ph.D. degree in science, mathematics, engineering, or technology fields:..... 0.00

Number of graduating undergraduates who achieved a 3.5 GPA to 4.0 (4.0 max scale): ...... 0.00

Number of graduating undergraduates funded by a DoD funded Center of Excellence grant for Education, Research and Engineering:..... 0.00

The number of undergraduates funded by your agreement who graduated during this period and intend to work for the Department of Defense ...... 0.00

The number of undergraduates funded by your agreement who graduated during this period and will receive scholarships or fellowships for further studies in science, mathematics, engineering or technology fields: ..... 0.00

<u>NAME</u>		
Total Number:		
	Names of personnel receiving PHDs	
<u>NAME</u>		
Total Number:		
	Names of other research staff	
<u>NAME</u>	PERCENT_SUPPORTED	
FTE Equivalent:		
Total Number:		

**Sub Contractors (DD882)** 

#### **Inventions (DD882)**

#### 5 High-Frequency Structures for Nanoelectronics and Molecular Electronics

Patent Filed in US? (5d-1) Y

Patent Filed in Foreign Countries? (5d-2)

Was the assignment forwarded to the contracting officer? (5e) N

Foreign Countries of application (5g-2):

5a: Chunrong Song

5f-1a: Clemson University

5f-c: 215 Riggs Hall

Clemson SC 29634

5a: Pingshan Wang

5f-1a: Clemson University

5f-c: 215 Riggs Hall

Clemson SC 29634

## Permalloy Film Array Spin Dynamics and High Performance Integrated Microwave Devices

Project: 2005567

**Final Report** 

Pingshan Wang

pwang@clemson.edu

#### **Project results**

- 1. Period of the project: (08/01/06-07/31/08)
- 2. Total amount of budget: \$50,000/24 months
- 3. Main achievements
  - a. Publications
    - i. Pingshan Wang, Hanqiao Zhang, Ralu Divan, Axel Hoffmann, "Tailoring High-Frequency Properties of Permalloy Films via Submicron Patterning", Accepted for publication in *IEEE Transactions on Magnetics*.
    - ii. Hanqiao Zhang, Chunrong Song and Pingshan Wang, "A new method for high-frequency characterization of patterned ferromagnetic thin films," submitted to *Journal of Applied Physics*.
    - iii. Hanqiao Zhang, Chunrong Song and Pingshan Wang, "A new method for high-frequency characterization of patterned ferromagnetic thin films," (abstract) accepted for presentation in 53<sup>rd</sup> Magnetism and Magnetic Material, 2008.
    - iv. Song, Chunrong; Liu, Zuqin; Eres, Gyula; Geohegan, David B.; Wang, Pingshan; "A New Method for Microwave Characterization of Metallic Single-Walled Carbon Nanotubes," <u>Nanotechnology</u>, 2008. NANO '08. 8th IEEE Conference on 18-21 Aug. 2008 Page(s):228 – 229
    - v. Zhang, Hanqiao; Song, Chunrong; Divan, Ralu; Hoffmann, Axel; Wang, Pingshan; "High-Frequency Properties of Permalloy Nanowire Arrays for RF Devices," Nanotechnology, 2008. NANO '08. 8th IEEE Conference on 18-21 Aug. 2008 Page(s):621 624.

#### b. Patent application:

- i. Pingshan Wang, Chunrong Song, "High-Frequency Structures for Nanoelectronics and Molecular Electronics", Application Serial No. or PCT Application No. 60/951,510, filing date 07/24/2007
- 4. Student supported: Hanqiao Zhang, Ph. D. student, began to work on the project since January, 2007.

#### Results not submitted for publication yet

1. FMR frequency dependence on transverse biasing field and DC current.

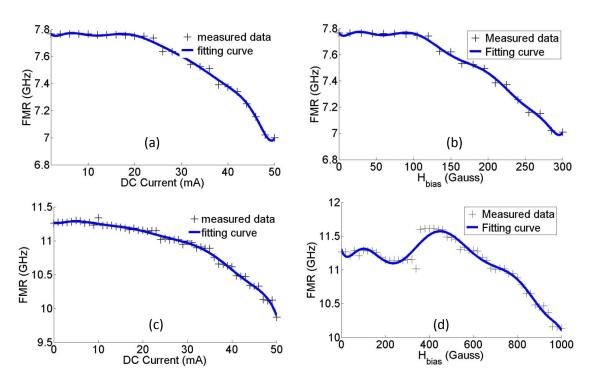


Fig. 1 FMR frequency dependence on DC current and external magnetic field. (a) and (b) are for 550 nm Py arrays. (c) and (d) are for 240 nm arrays. The reasons for the discrepancies between current excitation and field excitation are still under investigation.

#### 2. High-frequency inductor

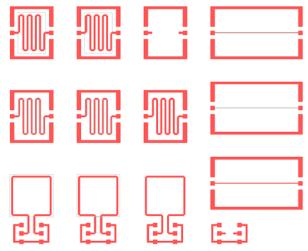


Fig. 2 Py loaded inductors (still under fabrication)